

**2-channel Read/Write Amplifier for GMR-Ind Head Hard Disk Drive**

**Description**

The CXA3541N is a read/write amplifier for GMR-Ind (Giant Magneto Resistive-Inductive) heads used in hard disk drives, and is capable of supporting up to two channels.

**Features**

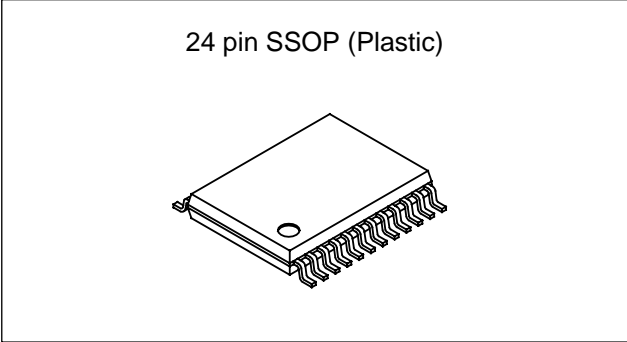
- +5V and -3V power supply
- Current bias voltage sense type
- Low power 180mW at read
- Differential read amplifier gain;  $\times 100/135$  ( $R_{MR} = 50\Omega$ )
- Input noise of  $0.77nV/\sqrt{Hz}$  (typ.),  $R_{MR} = 50\Omega$ ,  $I_B = 5.9mA$
- Recovery time write to read; 300ns (typ.)
- Write data is triggered by differential P-ECL signal
- Servo bank write
- Write unsafe detection circuit
- Serial port
  - Head selection
  - MR bias
  - Write current

**Applications**

Hard disk drives with GMR-Ind heads

**Structure**

Bipolar silicon monolithic IC



**Absolute Maximum Ratings** ( $T_a = 25^\circ C$ )

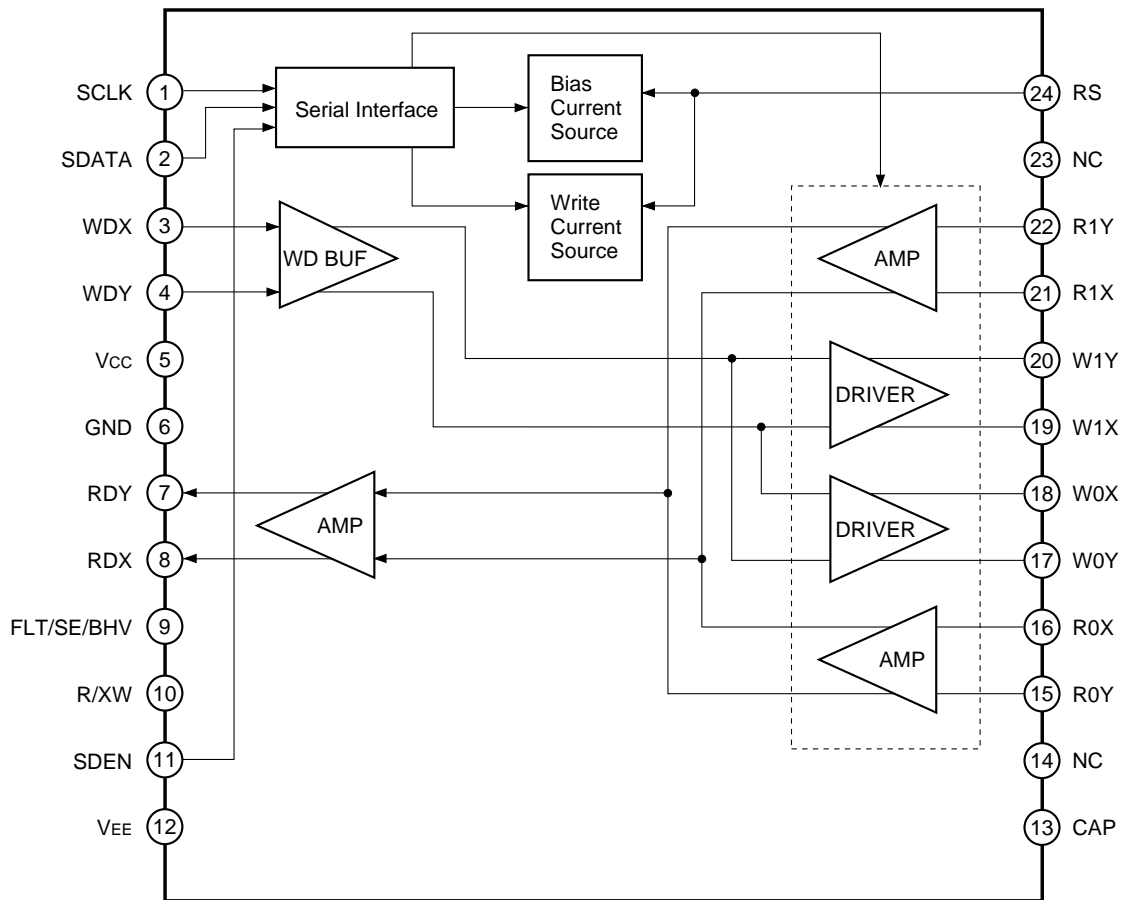
• Supply voltage	$V_{CC}$	-0.3 to +5.8	V
• Supply voltage	$V_{EE}$	-3.7 to +0.3	V
• Digital input voltage	$V_{di}$	-0.3 to $V_{CC} + 0.3$	V
• Operating temperature	$T_{opr}$	0 to +70	$^\circ C$
• Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$
• Allowable power dissipation	$P_D$	800	mW (on board)

**Operating Conditions**

• Supply voltage	$V_{CC}$	4.4 to 5.5	V
	$V_{EE}$	-3.5 to -2.6	V
• MR bias voltage	$V_{MR}$	-300 to +300	mV
• Bias current	$I_B$	3 to 8	mA
• Write current	$I_W$	19.5 to 49.5	mA

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Block Diagram and Pin Configuration



Pin Description

Pin No.	Symbol	Equivalent circuit	Description
1 2 11	SCLK SDATA SDEN		Serial control signal input.
3 4	WDX WDY		Differential P-ECL write data input.
5	Vcc		5V power supply.
6	GND		Ground.
7 8	RDY RDX		Read amplifier output with coupling capacitors. High impedance in the write mode.
9	FLT/SE/BHV		Head unsafe detection output. Servo bank write enable input. Buffered head voltage output.

Pin No.	Symbol	Equivalent circuit	Description
10	R/XW		Read/write control signal input. Read when high, write when low.
12	VEE		-3V power supply.
13	CAP		Connect an external capacitor of read amplifier between this pin and VEE.
14 23	NC		Non connection.
16 15 21 22	R0X R0Y R1X R1Y		MR heads for read. Two channels are provided.
18 17 19 20	W0X W0Y W1X W1Y		Inductive heads for write. Two channels are provided.

Pin No.	Symbol	Equivalent circuit	Description
24	RS		<p>Bias current setting register is connected between this pin and GND.</p>

**Electrical Characteristics**

(Unless otherwise specified;  $V_{CC} = 5V$ ,  $V_{EE} = -3V$ ,  $T_a = 25^{\circ}C$ ,  $CAP = 0.1\mu F$ ,  $R_S = 7.5k\Omega$ )

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
<b>Power Dissipation</b> $I_w = 29.5mA$ , $I_B = 5.9mA$							
1-1	V <sub>CC</sub> power supply current	ISP1	Sleep mode		2.15	2.85	mA
1-2		IID1	Idle mode		22	29	mA
1-3		IRE1	Read mode		37	48	mA
1-4		IWR1	Write mode		98	130	mA
1-5	V <sub>EE</sub> power supply current	IID2	Idle mode		10	13	mA
1-7		IRE2	Read mode		10	13	mA
1-8		IWR2	Write mode		10	13	mA
1-9	Bank write mode	ICCBW	$ICCBW = 17 + 17 \times N + I_w \times N$ $I_w = 29.5mA$	—	111	—	mA
<b>Digital Inputs</b>							
2-1	TTL input low input voltage	V <sub>IL</sub>	TTL input; R/XW Internal pull-up resistor	0		0.8	V
2-2	TTL input high input voltage	V <sub>IH</sub>		2.0		V <sub>CC</sub> + 0.3	V
2-3	TTL input input current	I <sub>TTL</sub>	High voltage: 5V Low voltage: 0V	-200		200	μA
2-4	Serial interface input low input voltage	V <sub>SIL</sub>	Serial input; SDATA, SCLK, SDEN			0.8	V
2-5	Serial interface input high input voltage	V <sub>SIH</sub>		2.35			V
2-6	Serial interface input input current	V <sub>ST</sub>	High voltage: 3.3V Low voltage: 0V Pull-down resistor: 14kΩ	-500		500	μA
3-1	P-ECL common voltage	V <sub>PC</sub>	(V <sub>H</sub> + V <sub>L</sub> )/2	1.55		V <sub>CC</sub>	V
3-2	P-ECL differential voltage	V <sub>PD</sub>	(V <sub>H</sub> - V <sub>L</sub> )	0.2		1.5	V
3-3	P-ECL high voltage	V <sub>PH</sub>				V <sub>CC</sub>	V
3-4	P-ECL input current	I <sub>WD</sub>	Input voltage: 4V	-20		20	μA
<b>Power Dissipation</b> $I_w = 29.5mA$ , $I_B = 5.9mA$							
4-1	Bank write enable voltage	V <sub>SEH</sub>		V <sub>CC</sub> + 1.2		V <sub>CC</sub> + 1.4	V
4-2	Bank write enable current	I <sub>SEH</sub>		6		14	mA
5-1	FLT output low voltage	V <sub>FLTL</sub>	Open collector output External resistance = 2.4kΩ			0.8	V
5-2	FLT output high voltage	V <sub>FLTH</sub>	Open collector output External resistance = 2.4kΩ	4.5			V
6	BHV gain accuracy	E <sub>BHV</sub>	$V_{BHV} = V_{CC} - 4 \times I_B \times (R_{MR} + 5.5\Omega)$ $I_B = "111"$ , $R_{MR} = 50\Omega$	-8		8	%

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
<b>Read Characteristics</b> $R_{MR} = 50\Omega$ , $I_B = 5.9mA$							
R1	Low gain	$A_{VL}$	Gain = 0 $R_{MR} = 50\Omega$ , $I_B = 5.9mA$	82	100	118	V/V
R2	High gain	$A_{VH}$	Gain = 1 $R_{MR} = 50\Omega$ , $I_B = 5.9mA$	110	135	160	V/V
R3	Low frequency cut-off (-3dB)	$F_{CL}$			350	550	kHz
R4	High frequency cut-off (-3dB)	$F_{CH}$		140	200		MHz
R5	Input reflected noise	$E_{Ni}$	Exclusive of head noise $R_{MR} = 50\Omega$ , $I_B = 5.9mA$		0.77	0.95	$\frac{nV}{\sqrt{Hz}}$
R6	MR bias current range 1	$I_{BR1}$		3		8	mA
R7	MR bias accuracy	$E_{IB}$		-7		+7	%
R8	MR bias resolution	$R_{IB}$	3-bit DAC	—	0.714	—	mA
R9-1	$V_{CC}$ power supply rejection ratio	PSRR1	Ripple voltage: 100mVp-p 100kHz to 50MHz	38			dB
R9-2	$V_{EE}$ power supply rejection ratio	PSRR2	Ripple voltage: 100mVp-p 100kHz to 10MHz	45			dB
R10-1	Common mode rejection ratio 1	CMRR1	Ripple voltage: 100mVp-p 100kHz to 50MHz	37			dB
R10-2	Common mode rejection ratio 2	CMRR2	Ripple voltage: 100mVp-p 51MHz to 80MHz	27			dB
R11	Control line input noise rejection	CLRR	Ripple voltage: 100mVp-p 4MHz to 80MHz	40			dB
R12	RDX/RDY offset difference magnitude	$V_{OFF1}$	Write to read			50	mV
R13	RDX/RDY output impedance	$R_{Dro}$	Differential, read mode	30		100	$\Omega$
<b>Read Safety Characteristics</b>							
P1	MR head open threshold	MRop	Head X – Head Y	600	750	900	mV
P2	MR head short threshold	MRsh	Head X – Head Y $I_B = "000"$ to $"011"$	15	50	90	mV
<b>Write Characteristics</b>							
W1	Write current range	$I_{WR}$	DAC code = x "0000" to x "1111"	19.5		49.5	mA
W2	Write current accuracy	$E_{IW}$	$R_H = 0\Omega$	-7		+7	%
W3	Write current resolution	$R_{IW}$	4-bit DAC	—	2	—	mA
W4	Leakage current	$I_{LEAK}$	Unselected head			200	$\mu A$
W6	Damping resistor	$R_D$		800	1000	1200	$\Omega$
W7	Write current propagation delay time	$T_{pd}$	$L_H = 0$ , $R_H = 0$ Write data to 50% of write current			10	ns
W8	Write current rise/fall time	$T_R/T_F$	$R_H = 15\Omega$ , $L_H = 150nH$ , $I_W = 25mA$	—	1.9	—	ns
W9	Erase current accuracy	$E_{IE}$	$V_{CC} = 3.5V$ DAC code = x "0101"	-18	-9	0	%
W10	Bank write current accuracy		Refer to Fig.				

No.	Item	Symbol	Measurement conditions	Min.	Typ.	Max.	Unit
<b>Write Safety Characteristics</b>							
U1	Write head open threshold	Rop	Detect open head		1.2	1.4	V
U2	Head voltage when short to GND	V <sub>G</sub>	Detect short to GND			0.1	V
U3	WD frequency too low	f <sub>WDL</sub>		0.5		1.8	MHz
U4	Write safety detect time	T <sub>WS</sub>	T1: 2 transitions on WDX/WDY			300 + T1	ns
U5	Low V <sub>CC</sub> threshold	V <sub>WthL</sub>	Fault detected	3.7	3.9	4.1	V
U6	Low V <sub>CC</sub> threshold	V <sub>WthH</sub>	Fault removed	3.9	4.1	4.3	V
U7	Low V <sub>CC</sub> threshold hysteresis	V <sub>hys</sub>		—	200	—	mV
<b>Switching Characteristics</b> I <sub>w</sub> = 29.5mA, I <sub>B</sub> = 5.9mA							
S1	Write to Read	T <sub>WR</sub>	Signal on WDX/WDY 90% RD signal or 10% I <sub>w</sub>		300	500	ns
S2	Read to Write	T <sub>RW</sub>	90% I <sub>w</sub>		50	70	ns
S3	Idle to Read	T <sub>IR</sub>	90% RD signal			1.0	μs
S4	Sleep to Read	T <sub>SR1</sub>	90% RD signal, 90% I <sub>B</sub> *1 I <sub>B</sub> = "011"		600	2000	μs
<b>Bank Write Characteristics</b> I <sub>w</sub> = 29.5mA, I <sub>B</sub> = 5.9mA							
S5	Read to Bank write	T <sub>RB</sub>	90% I <sub>w</sub>			100	ns
S6	Bank write to Read	T <sub>BR</sub>	10% I <sub>w</sub>			100	ns
S7	Idle to Bank write Idle to Write	T <sub>IW</sub>	90% I <sub>w</sub>			300	μs
<b>Serial Port Timing</b>							
B1	Setup time	T <sub>SU</sub> (sden)	SDEN to first SCLK	30			ns
B2	Hold time	T <sub>H</sub> (sden)	Last SCLK to deassert SDEN	15			ns
B4	SCLK frequency	f (sclk)				30	MHz
B5	SCLK pulse width	T <sub>w</sub> (sclk)		10			ns
B6	SCLK – SDATA setup time	T <sub>SU</sub> (d)		10			ns
B7	SCLK – SDATA hold time	T <sub>H</sub> (d)		10			ns
B8	SDEN low time	T <sub>SL</sub>		100			ns

\*1 T<sub>SR</sub> is proportional to I<sub>B</sub> and external CAP value.

**Serial Port Characteristics**

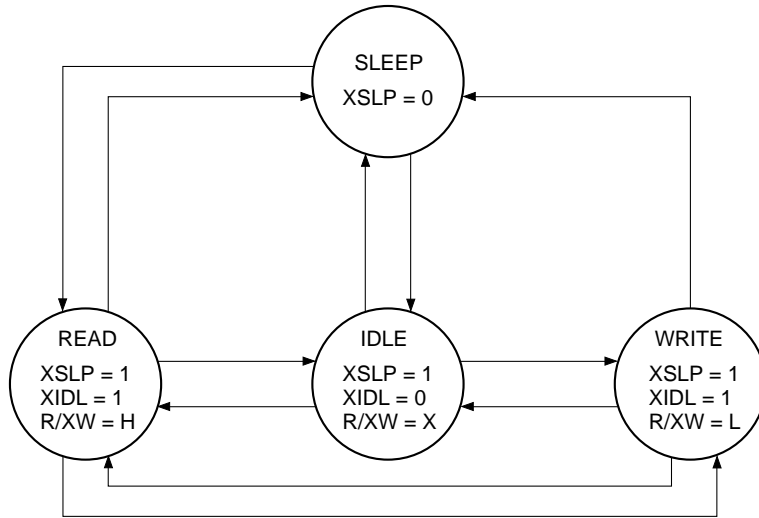
ADR1	ADR0	DATA5	DATA4	DATA3	DATA2	DATA1	DATA0
0	0	XSLP	XIDL	N/A	N/A	N/A	HS
0	1	GAIN	BHV	N/A	IB2	IB1	IB0
1	0	MROPN	MRSHT	IW3	IW2	IW1	IW0

\* IB[2:0] bits are initialized by "0" at power on.

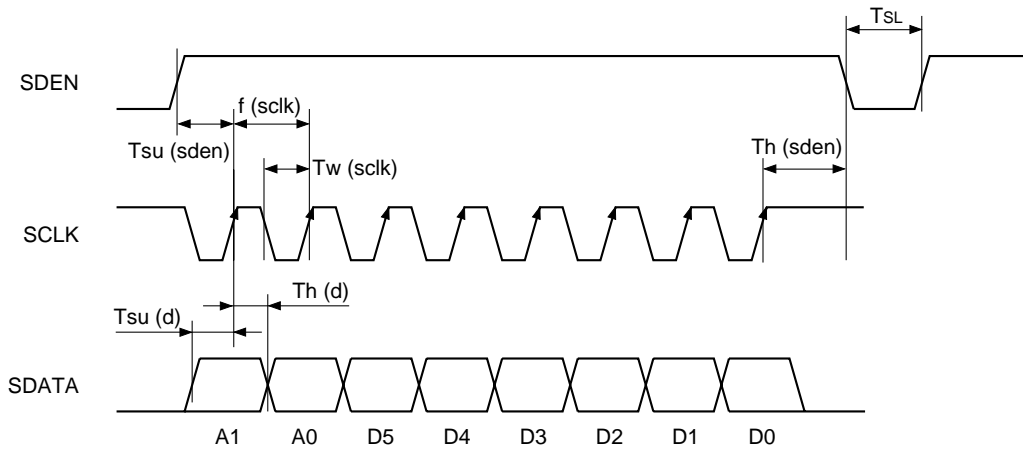
**Code Description**

Bit	Function
XSLP	0 = Set the pre-amplifier into low power "sleep" mode.
XIDL	0 = Set pre-amplifier to idle mode.
HS	Head select bit.
GAIN	Set the pre-amplifier to high or low gain mode. 1 = Set pre-amplifier to high gain mode.
BHV	Active the BHV test point pin. "1" active.
IB[2:0]	MR bias current set.
MROPN	1 = Set MR head open detector active.
MRSHT	1 = Set MR head short detector active.
IW[3:0]	Set write current.

Mode Control



Serial Port Timing Detail



Serial Port Timing

After the SDEN goes high, the last eight bits are transferred into the register. The SCLK will shift the data presented at SDATA into an internal shift register on the rising edge of each clock. As SCLK initial condition, both of low and high signal is acceptable.

### Unsafe Condition

1. Write fault condition  
FLT is a high level in write fault condition.
  - Open write head leads.  $f_{WD} < 15\text{MHz}$
  - Write head leads shorted to ground.
  - WD frequency is too low.
  - Power supply is out of tolerance.
2. Read fault condition  
FLT is a low level in read fault condition.
  - Open short MR head. (This function is set by serial resistor.)

### Bank Write Control (Refer to Bank "Write current vs. Current accuracy" characteristic curve)

1. Set the read mode.
2. Force a certain voltage (min.  $V_{CC} + 1.2\text{V}$ ) to FLT/SE pin by using the pull-up register. ( $R_{SE} = 820\Omega$ )  
#This operation disables all fault detection.
3. Set  $V_{CC}$  at 3.5V (in case of the erase mode only)
4. Start the write operation by setting R/XW = L.
5. Terminate the write operation by setting R/XW = H.
  - i) Allow 50% write duty or less.
  - ii) Low voltage detector is disabled in the bank write mode and erase mode.
  - iii) Don't change the serial register data bits in following conditions:
    - $V_{CC} = 3.5\text{V}$
    - On entering write data.

### BHV (Buffered Head Voltage)

1. Applicable within  $V_{CC} = 5\text{V} \pm 5\%$ .
2. Turn BHV on, but turn off MROPN and MRSHT.
3.  $V_{BHV}$  is determined by basis of  $V_{CC}$ .  $V_{BHV} = V_{CC} - (4 \times I_B \times (R_{MR} + 5.5\Omega))$

### Head Condition

1. Short X-Y terminal on un-used write head.
2. Recommended X-Y terminal on un-used read head short.

### Polarity

1. Read output signal on RDX is negative, when MRX is positive by increasing  $R_{MR}$ .
2. Write current flows into X side, when WDX is high and WDY is low.

### Head Select Table

(2ch)

HS	Normal operation
0	0
1	1

**MR Bias**

IB2	IB1	IB0	I <sub>B</sub> [mA]
0	0	0	3.0
0	0	1	3.714
0	1	0	4.429
0	1	1	5.143
1	0	0	5.857
1	0	1	6.571
1	1	0	7.286
1	1	1	8.0

**Write Current**

IW3	IW2	IW1	IW0	Write current [mA <sub>0-P</sub> ]
0	0	0	0	19.5
0	0	0	1	21.5
0	0	1	0	23.5
0	0	1	1	25.5
0	1	0	0	27.5
0	1	0	1	29.5
0	1	1	0	31.5
0	1	1	1	33.5
1	0	0	0	35.5
1	0	0	1	37.5
1	0	1	0	39.5
1	0	1	1	41.5
1	1	0	0	43.5
1	1	0	1	45.5
1	1	1	0	47.5
1	1	1	1	49.5

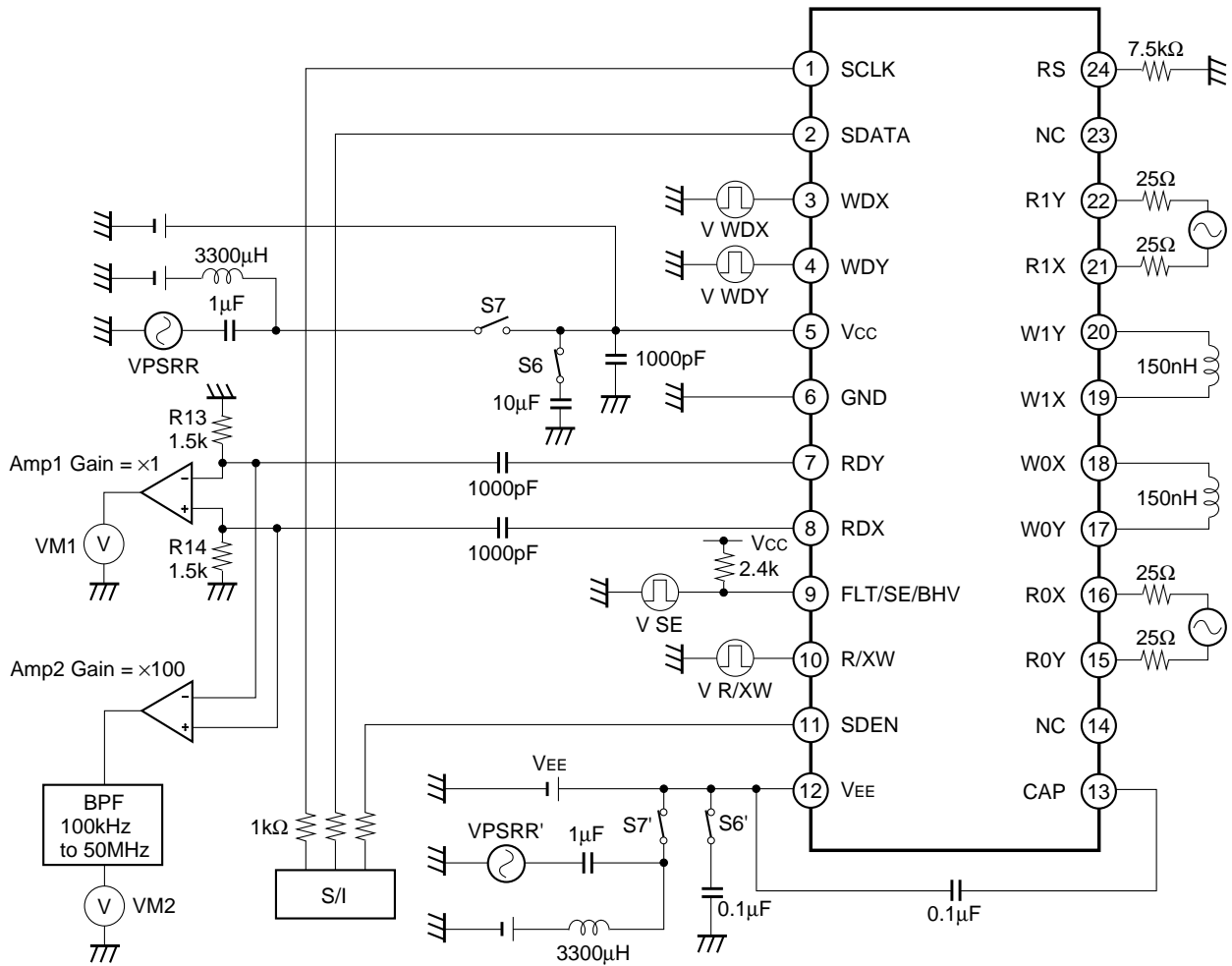
Actual head current is defined by the following equation:

$$I_{\text{HEAD}} = I_w / (1 + R_H/R_D)$$

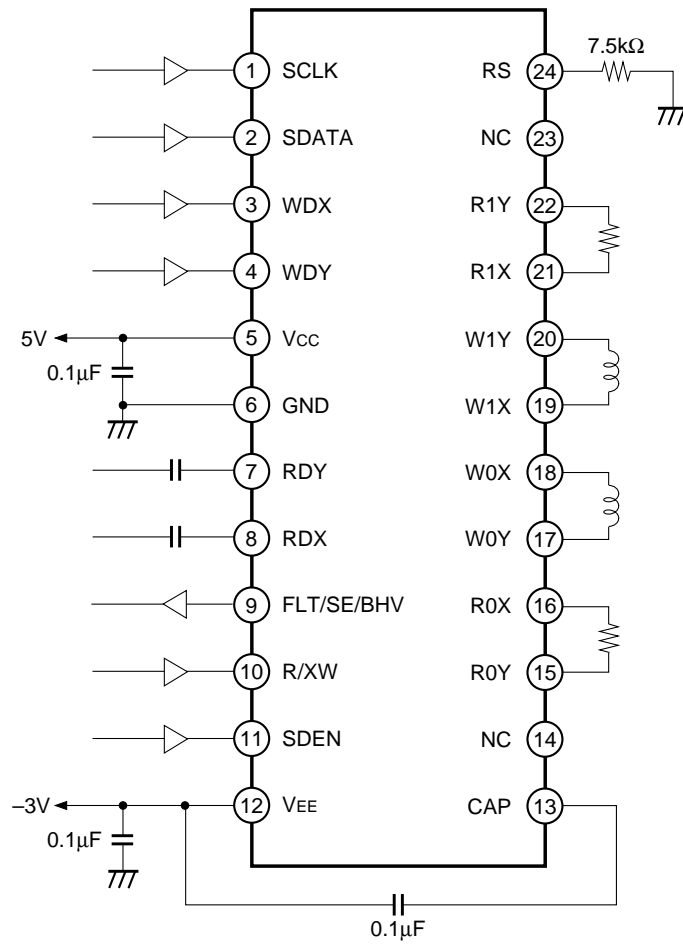
R<sub>H</sub>: Head resistance

R<sub>D</sub>: Damping resistance

Electrical Characteristics Measurement Circuit

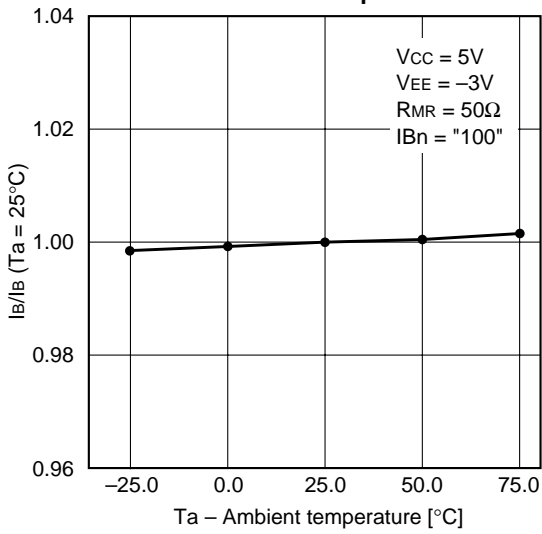


Application Circuit

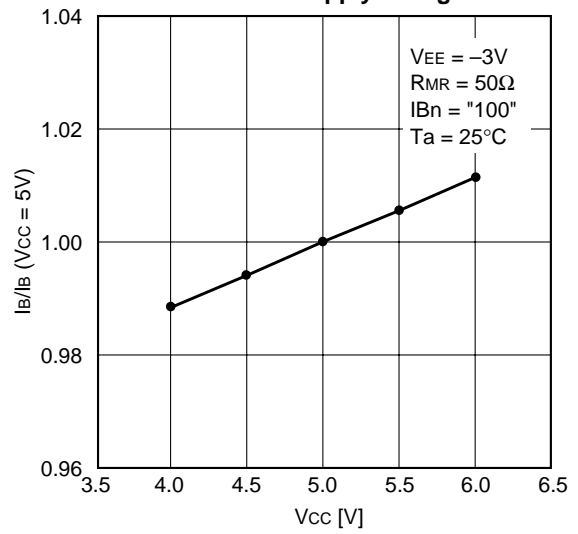


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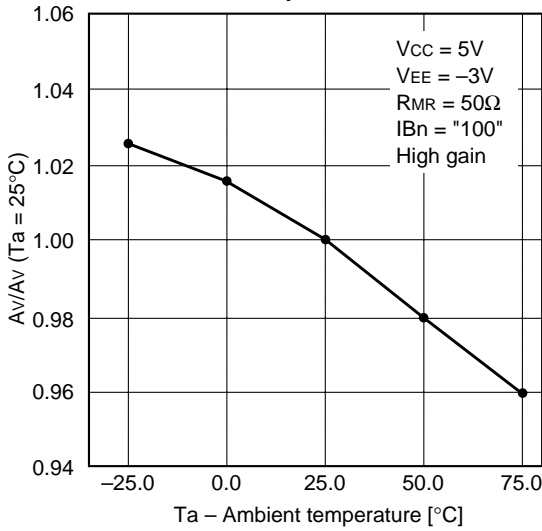
**Normalized bias current vs. Ambient temperature**



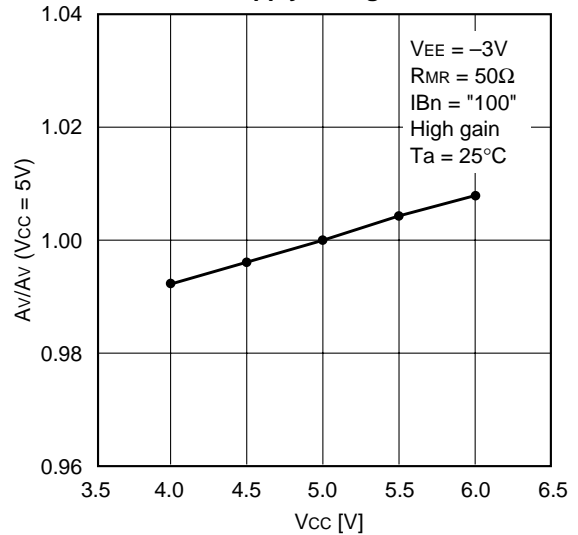
**Normalized bias current vs. Power supply voltage**



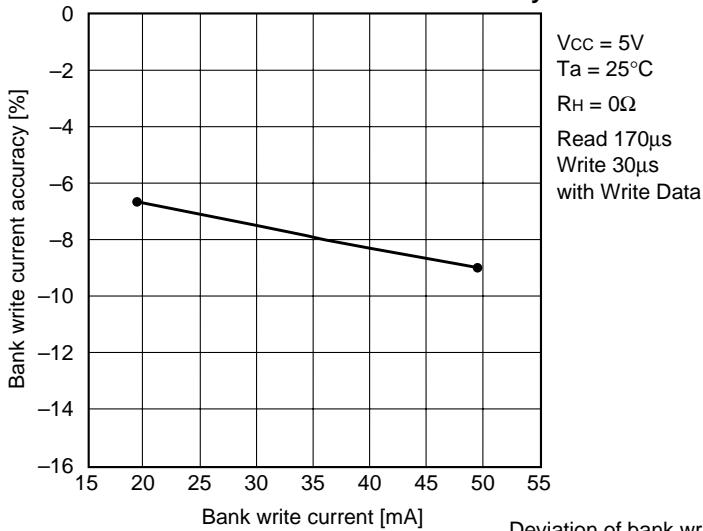
**Normalized read amplifier voltage gain vs. Ambient temperature**



**Normalized read amplifier voltage gain vs. Power supply voltage**

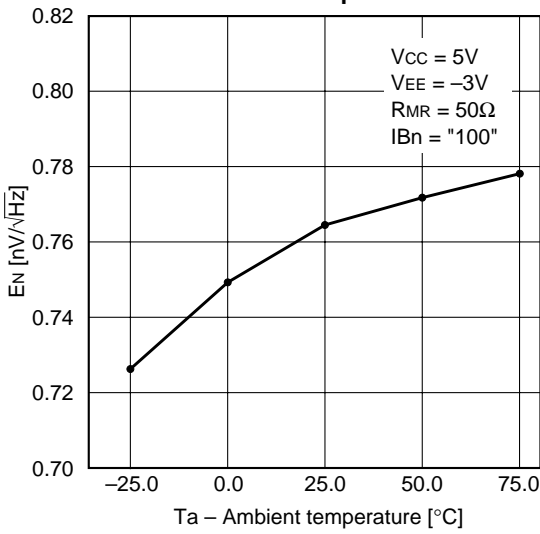


**Bank write current vs. Current accuracy**

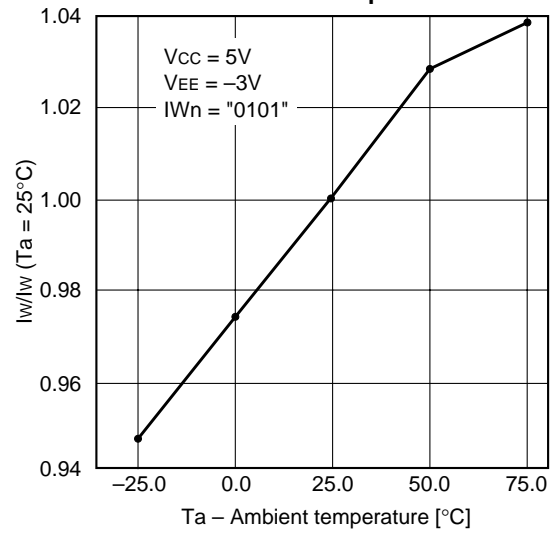


Deviation of bank write current is within ± 7% at basis of the chart.

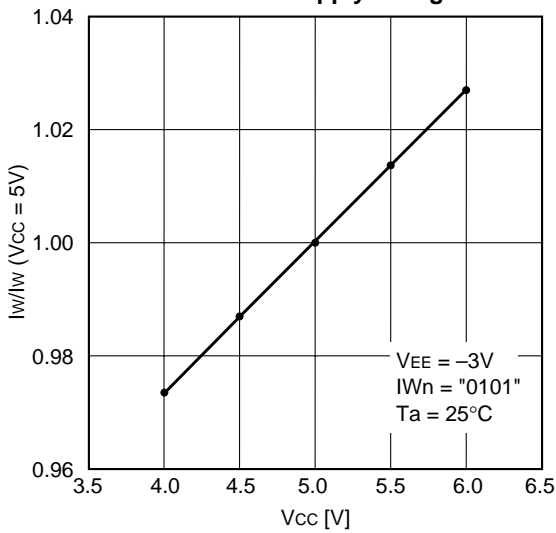
**Input referred noise voltage vs. Ambient temperature**



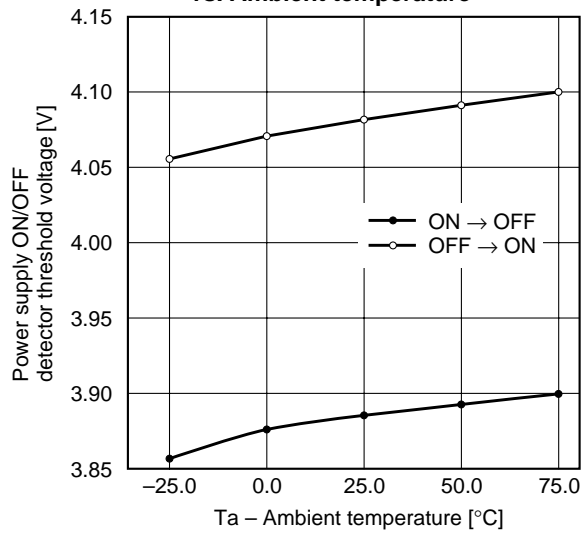
**Normalized write current vs. Ambient temperature**



**Normalized write current vs. Power supply voltage**



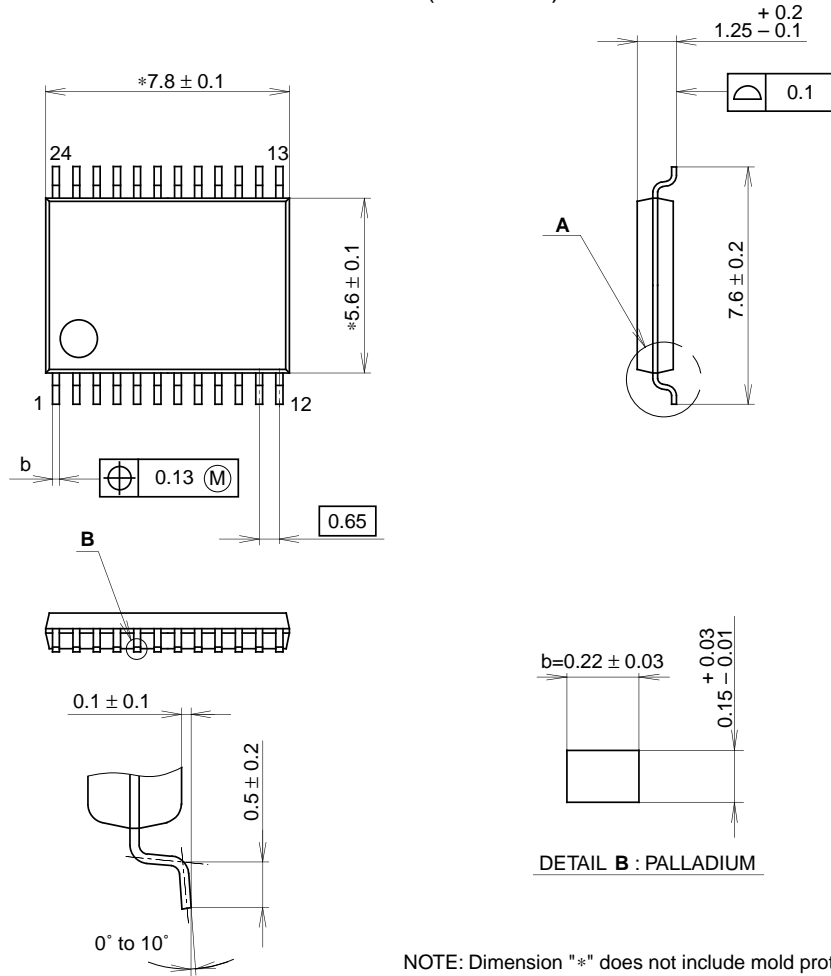
**Power supply ON/OFF detector threshold voltage vs. Ambient temperature**



Package Outline

Unit: mm

24PIN SSOP (PLASTIC)



DETAIL A

DETAIL B : PALLADIUM

NOTE: Dimension "\*" does not include mold protrusion.

SONY CODE	SSOP-24P-L01
EIAJ CODE	P-SSOP24-7.8x5.6-0.65
JEDEC CODE	_____

PACKAGE STRUCTURE

PACKAGE MATERIAL	EPOXY RESIN
LEAD TREATMENT	PALLADIUM PLATING
LEAD MATERIAL	COPPER ALLOY
PACKAGE MASS	0.1g



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